Silicon NPN Power Transistors 2SC1108

DESCRIPTION

- With TO-220C package
- High breakdown voltage :V_{CEO}=100V
- High current :4A

APPLICATIONS

- For power amplifier applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

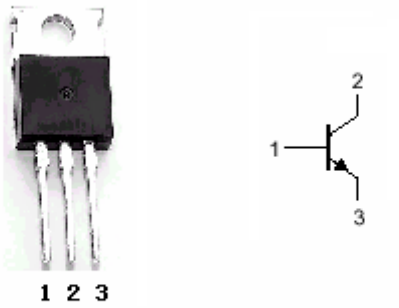

Fig.1 simplified outline (TO-220C) and symbol

Absolute maximum ratings(Tc=25℃)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	100	V
V_{CEO}	Collector-emitter voltage	Open base	100	V
V_{EBO}	Emitter-base voltage	Open collector	5	V
I_C	Collector current		4	A
P_C	Collector power dissipation	T_C=25℃	40	W
T_j	Junction temperature		150	℃
T_{stg}	Storage temperature		-55~150	℃

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CHARACTERISTICS

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	I_C=25mA; I_B=0	100			V
$V_{(BR)EBO}$	Emitter-base breakdown votage	I_E=1mA; I_C=0	5			V
V_{CEsat}	Collector-emitter saturation voltage	I_C=3A;I_B=0.3 A			1.5	V
V_{BEsat}	Base-emitter saturation voltage	I_C=3A;I_B=0.3 A			2.0	V
I_{CBO}	Collector cut-off current	V_{CB}=100V; I_E=0			0.1	mA
I_{EBO}	Emitter cut-off current	V_{EB}=5V; I_C=0			0.1	mA
h_{FE}	DC current gain	I_C=1A ; V_{CE}=4V	100		320	
f_T	Transition frequency	I_C=0.5A ; V_{CE}=12V		10		MHz
C_{OB}	Output capacitance	I_E=0; V_{CB}=10V;f=1MHz	25			pF

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PACKAGE OUTLINE

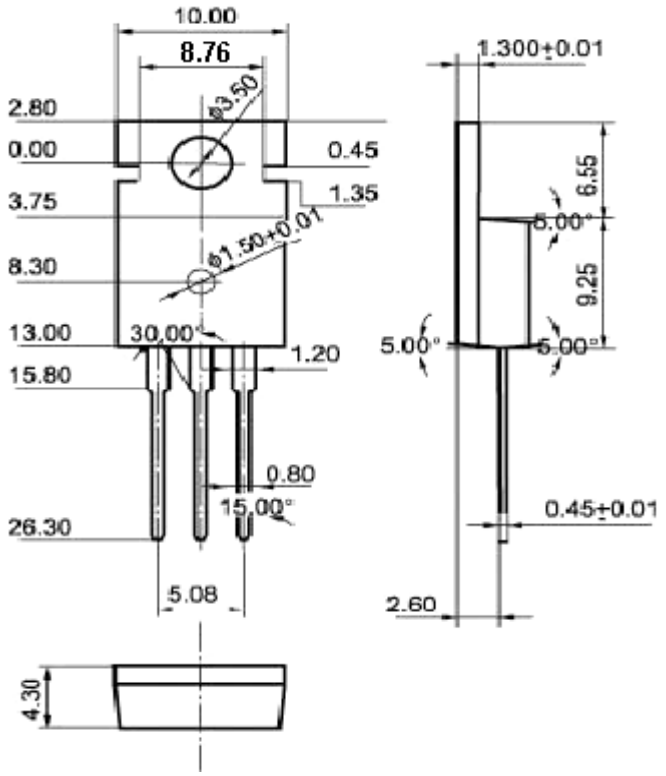

Fig.2 Outline dimensions (unindicated tolerance:±0.10 mm)